

MRT200.22

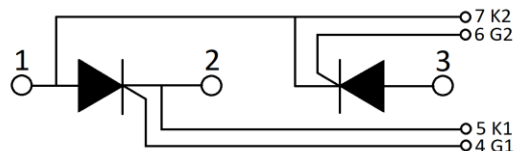
Thyristors module

Features:

- International standard package
- High surge capability
- Glass passivated chip
- Simple mounting
- UL recognized, file no. E312789

Typical applications:

- Power converters
- Lighting control
- AC/DC motor control and drives
- Heat and temperature control



Symbol	Characteristics	Test Conditions	Value			Unit
			Min	Typ	Max	
$V_{RSM/DSM}$	Non-repetitive reverse/forward blocking voltage	$T_j = 25^{\circ}\text{C}$			2300	V
$V_{RRM/DRM}$	Repetitive reverse/forward blocking voltage	$T_j = 25^{\circ}\text{C}$			2200	V
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz			200 (182)	A
$I_{T(RMS)}$	RMS on-state current	$T_c = 75^{\circ}\text{C}$ (85 °C)			314 (286)	A
I_{RRM} I_{DRM}	Repetitive peak current	at V_{DRM}/V_{RRM} $T_j = 125^{\circ}\text{C}$			25	mA
I_{TSM}	Surge non repetitive current	10ms half sine wave $T_j = 45^{\circ}\text{C}$			4700	A
$I^2 t$	$I^2 t$ for fusing coordination	10ms half sine wave $V_R = 60\% V_{RRM}$ $T_j = 45^{\circ}\text{C}$			110000	A ² s
V_{TO}	Threshold voltage	$T_j = 125^{\circ}\text{C}$			0.85	V
r_T	On-state slope resistance	$T_j = 125^{\circ}\text{C}$			1.21	mΩ
V_{TM}	Peak on-state voltage	$T_j = 25^{\circ}\text{C}$; $I_T = 550\text{A}$			1.96	V
dv/dt	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM}$, $T_j = 125^{\circ}\text{C}$, linear voltage rise			1000	V/μs
di/dt	Critical rate of rise of off-state current	$T_j = 125^{\circ}\text{C}$, Gate source 1,5A, $T_r < 0,5\mu\text{s}$ Repetitive			200	A/μs
I_{GT}	Gate trigger current	$V_A = 12\text{V}$, $I_A = 1\text{A}$, $T_j = 25^{\circ}\text{C}$	30		150	mA
V_{GT}	Gate trigger voltage		0,7		2.5	V
I_H	Holding current		10		200	mA
I_L	Latching current				1000	mA
V_{GD}	Non-trigger gate voltage	$V_{DM} = 67\% V_{DRM}$, $T_j = 125^{\circ}\text{C}$			0.20	V
$R_{th(j-c)}$	Thermal resistance junction to case	Single side cooled per chip			0.16	°C/W
$R_{th(c-s)}$	Thermal resistance case to sink	Single side cooled per chip			0.08	°C/W
V_{ISO}	Isolation voltage	50Hz, RMS, t = 1min, $I_{ISO} : 1\text{mA}$ (MAX)		3000		V
F_M	Mounting torque - copper plate (M6)		4		6	N·m
	Mounting torque - terminal (M6)		4		6	N·m
T_{stg}	Storage Temperature		-40		125	°C
T_j	Operating Temperature		-40		125	°C
W_t	Weight			320		g
Outline	216F3					

On-state voltage Vs. peak on-state current

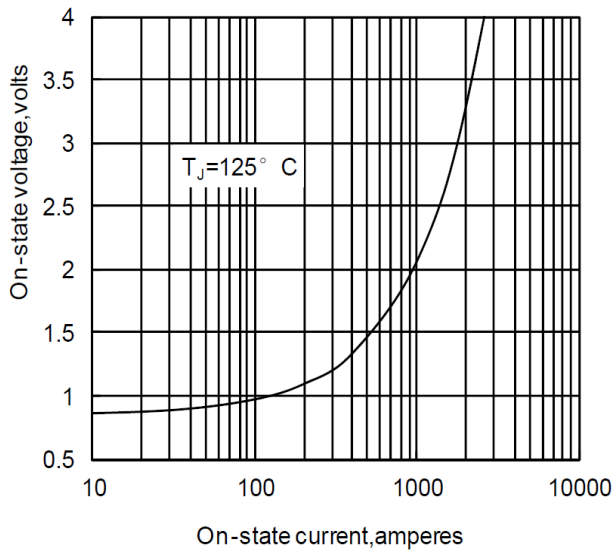


Fig. 1

Max. junction to case thermal impedance Vs. time

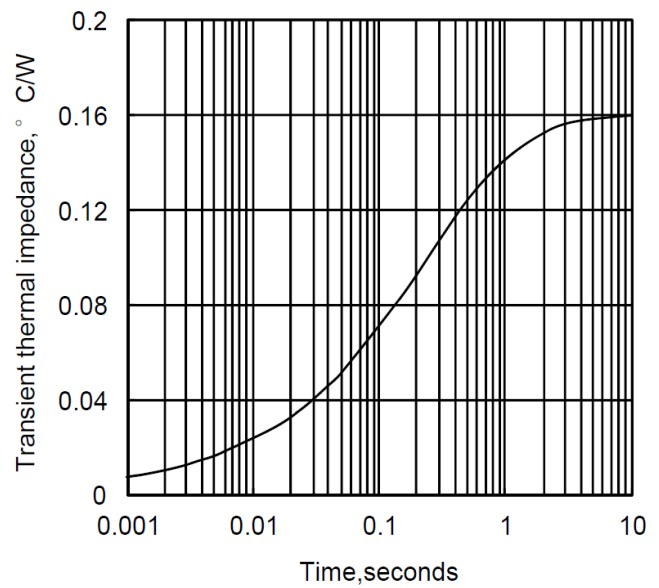


Fig. 2

Max. power dissipation Vs. mean on-state current

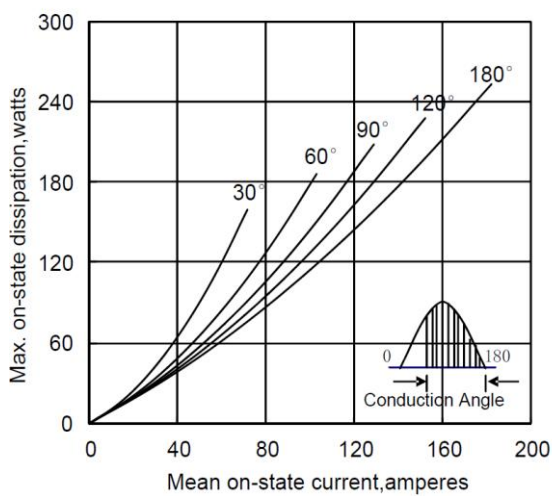


Fig. 3

Max. case temperature Vs. mean on-state current

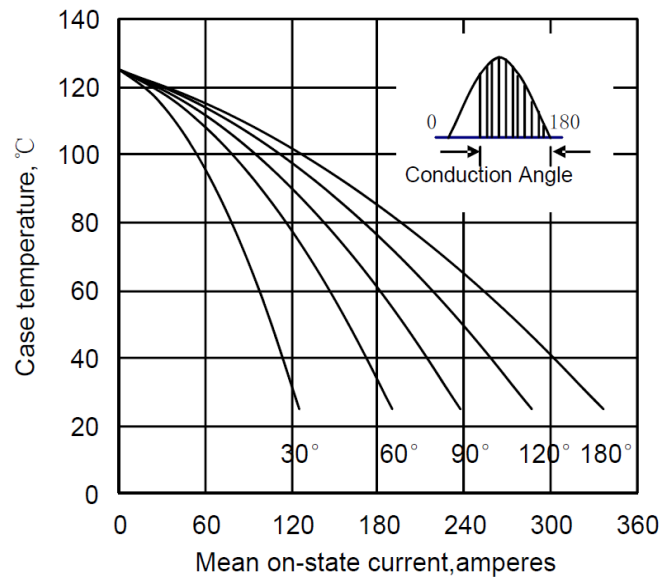


Fig. 4

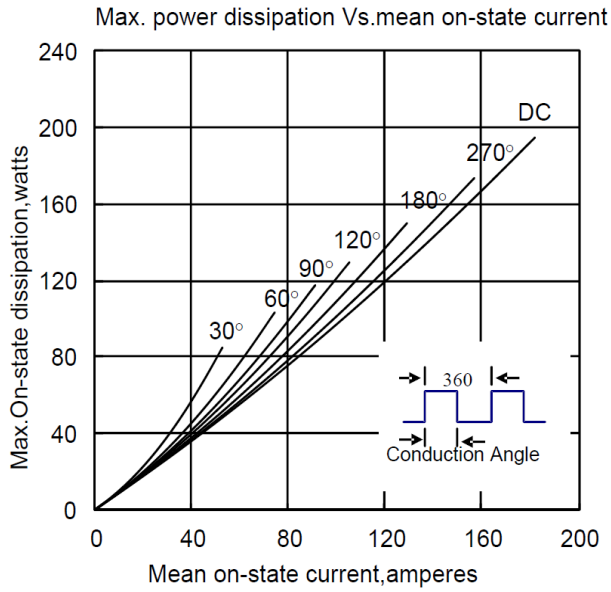


Fig. 5

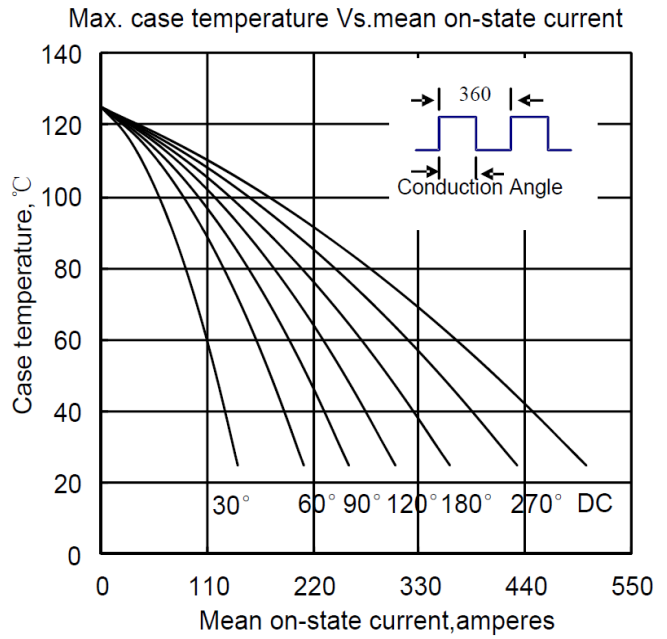


Fig. 6

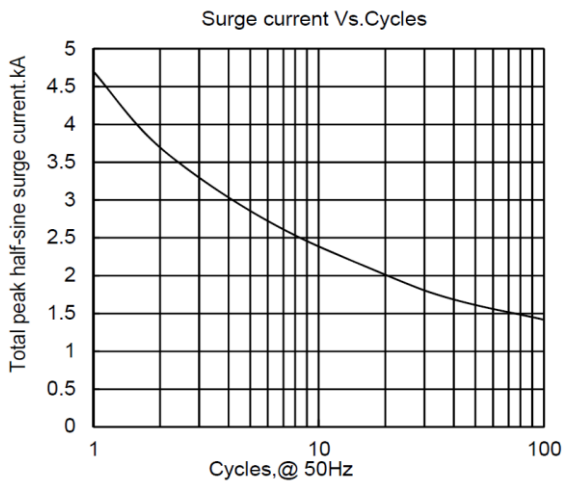


Fig. 7

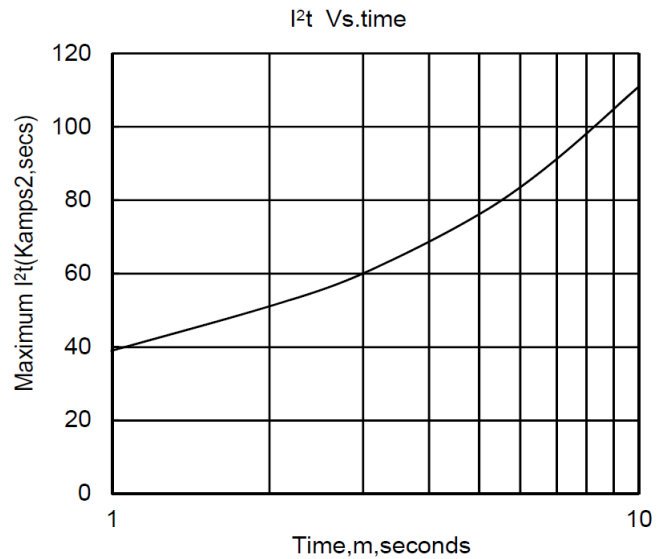


Fig. 8

Gate trigger characteristics

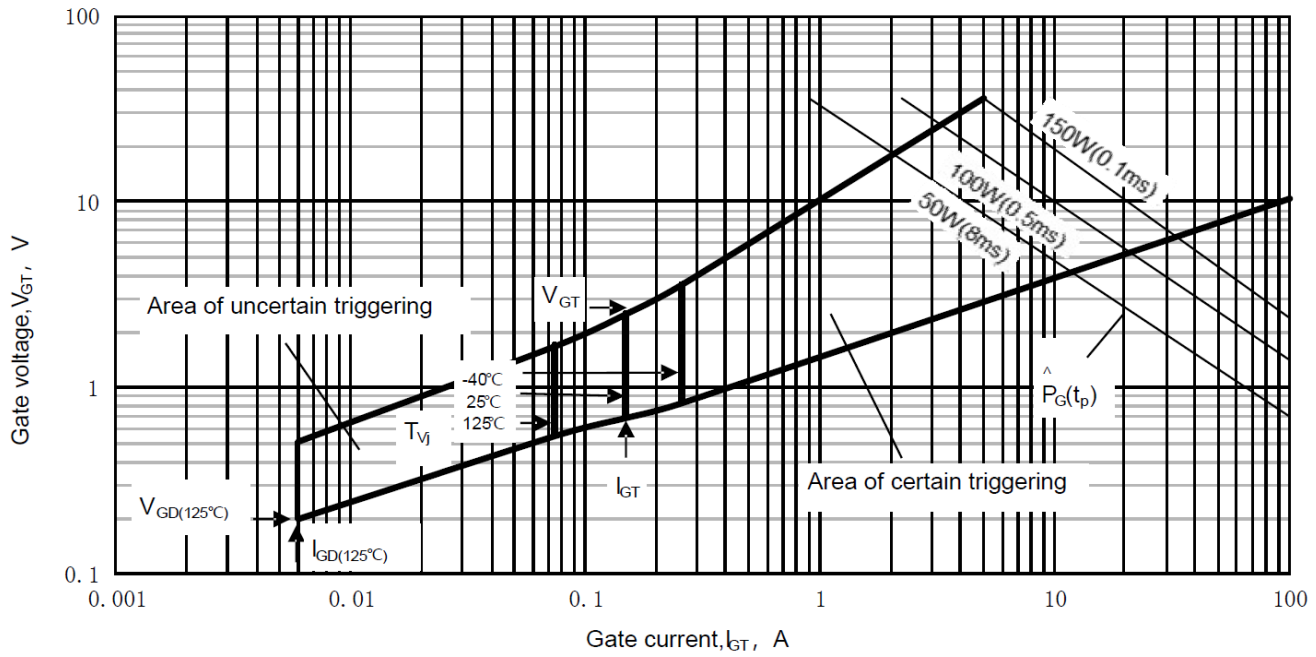
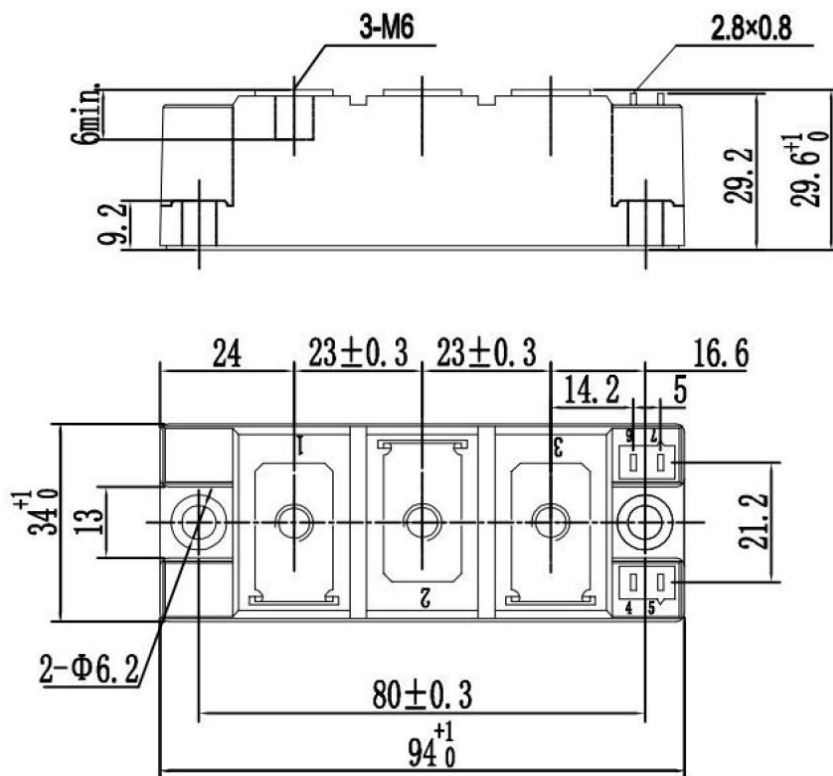


Fig.9



(dimensions in mm)

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Scomes Srl reserves the right to change any specification without notice